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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p125-1vq100t

Advanced Architecture

The proprietary Automotive ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The Automotive ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM memory
- Extensive CCCs and PLLs
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the Automotive ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

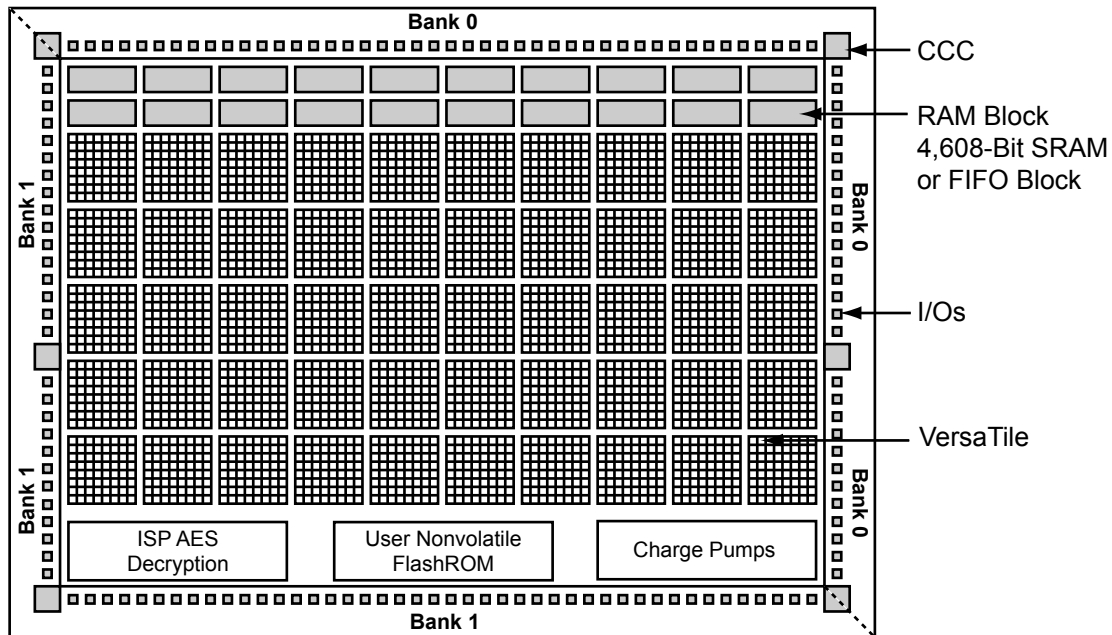


Figure 1-1 • Automotive ProASIC3 Device Architecture Overview with Two I/O Banks (A3P060 and A3P125)

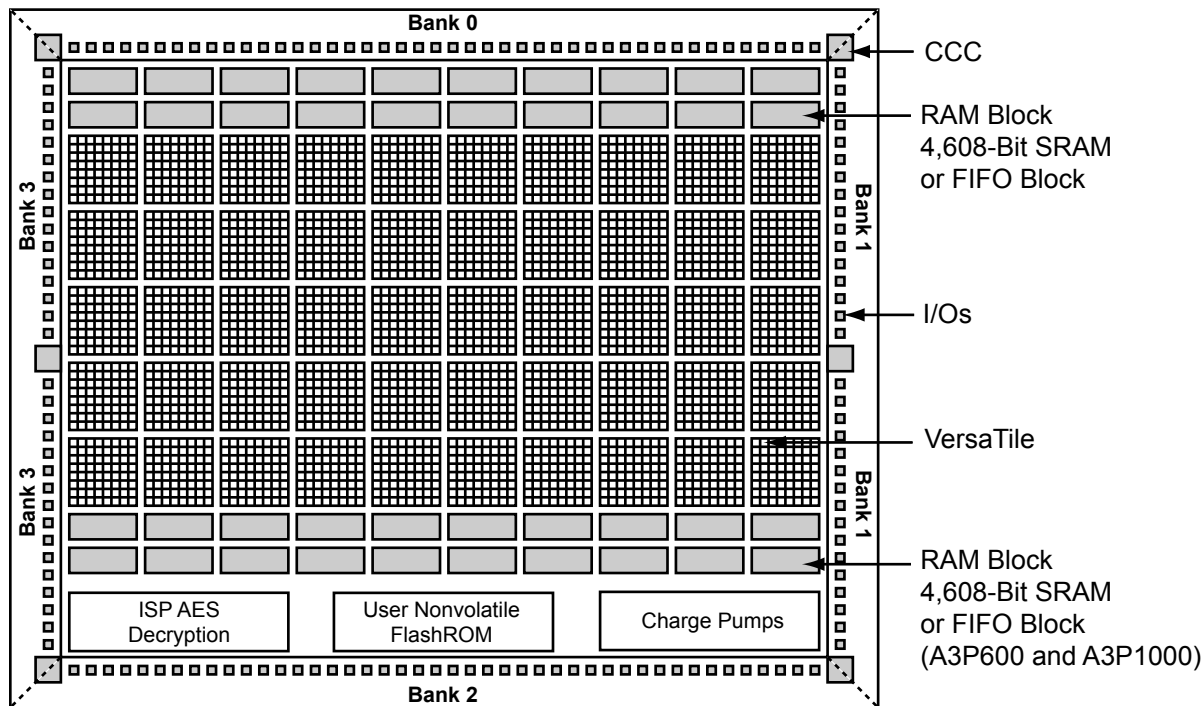


Figure 1-2 • Automotive ProASIC3 Device Architecture Overview with Four I/O Banks (A3P600 and A3P1000)

VersaTiles

The Automotive ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The Automotive ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

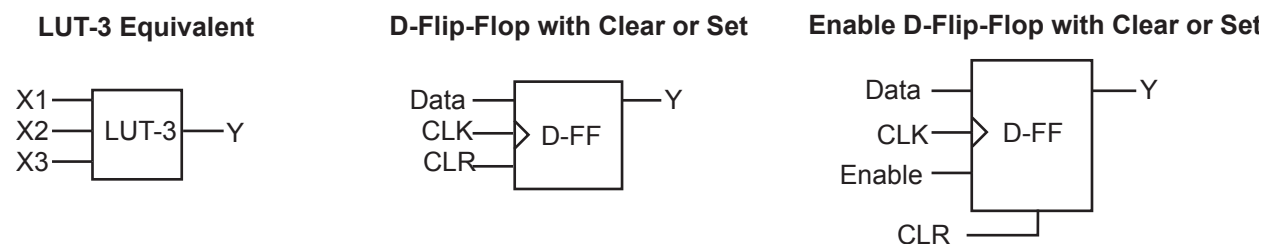


Figure 1-3 • VersaTile Configurations

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × 350 MHz / f_{OUT_CCC} (for PLL only)

Global Clocking

Automotive ProASIC3 devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

The Automotive ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). Automotive ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

Automotive ProASIC3 banks for the A3P250 and A3P1000 devices support LVPECL, LVDS, B-LVDS, and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the [FlashPro User's Guide](#) for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify ([Figure 1-4 on page 1-7](#)).

Table 2-3 • Overshoot and Undershoot Limits (as measured on quiet I/Os)

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle	Maximum Overshoot/Undershoot (115°C)	Maximum Overshoot/Undershoot (135°C)
2.7 V or less	10%	0.81 V	0.72 V
	5%	0.90 V	0.82 V
3 V	10%	0.80 V	0.72 V
	5%	0.90 V	0.81 V
3.3 V	10%	0.79 V	0.69 V
	5%	0.88 V	0.79 V
3.6 V	10%	N/A	N/A
	5%	N/A	N/A

Notes:

1. The duration is allowed at one out of six clock cycles (estimated SSO density over cycles). If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
2. This table refers only to overshoot/undershoot limits for simultaneously switching I/Os and does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC[®]3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-4](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-4](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.2 V

Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.1 V

Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to V_{CCL}.
- JTAG supply, PLL power supplies, and charge pump V_{PUMP} supply have no influence on I/O behavior.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

Power Consumption of Various Internal Resources

Table 2-11 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices

Parameter	Definition	Device Specific Dynamic Power (μW/MHz)			
		A3P1000	A3P250	A3P125	A3P060
PAC1	Clock contribution of a Global Rib	14.50	11.00	11.00	9.30
PAC2	Clock contribution of a Global Spine	2.48	1.58	0.81	0.81
PAC3	Clock contribution of a VersaTile row	0.81			
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12			
PAC5	First contribution of a VersaTile used as a sequential module	0.07			
PAC6	Second contribution of a VersaTile used as a sequential module	0.29			
PAC7	Contribution of a VersaTile used as a combinatorial module	0.29			
PAC8	Average contribution of a routing net	0.70			
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-7 on page 2-6 .			
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-7 and Table 2-10 on page 2-8 .			
PAC11	Average contribution of a RAM block during a read operation	25.00			
PAC12	Average contribution of a RAM block during a write operation	30.00			
PAC13	Static PLL contribution	2.55 mW			
PAC14	Dynamic contribution for PLL	2.60			

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in [Table 2-12 on page 2-11](#).
- Enable rates of output buffers—guidelines are provided for typical applications in [Table 2-13 on page 2-12](#).
- Read rate and write rate to the memory—guidelines are provided for typical applications in [Table 2-13 on page 2-12](#). The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Table 2-21 • Summary of I/O Timing Characteristics—Software Default Settings
–1 Speed Grade, Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$
Worst Case $V_{CCI} = 3.0\text{ V}$
Standard Plus I/O Banks

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor	t_{bOUT}	t_{bP}	t_{bIN}	t_{pY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.05	0.04	1.23	0.39	3.11	2.99	1.56	1.69	5.23	5.11	ns
1.8 V LVCMOS	8 mA	High	35 pF	–	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.99	ns
1.5 V LVCMOS	4 mA	High	35 pF	–	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.18	ns
3.3 V PCI	Per PCI spec	High	10 pF	25^2	0.55	2.19	0.04	0.81	0.39	1.27	0.94	2.65	3.06	1.27	0.94	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25^2	0.55	2.19	0.04	0.79	0.39	1.27	0.94	2.65	3.06	1.27	0.94	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.
2. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-48](#) for connectivity. This resistor is not required during normal operation.

Table 2-31 • I/O Input Rise Time, Fall Time, and Related I/O Reliability

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS	No requirement	10 ns *	20 years (110°C)
LVDS/B-LVDS/M-LVDS/LVPECL	No requirement	10 ns *	10 years (100°C)

Note: **The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure there is no excessive noise coupling into input signals.*

Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.63	7.79	0.05	1.08	0.45	7.94	6.80	1.22	1.23	7.94	6.80	ns
	-1	0.55	6.85	0.04	0.95	0.39	6.98	5.98	1.26	1.27	6.98	5.98	ns
6 mA	STD	0.63	4.87	0.05	1.08	0.45	4.96	4.13	1.38	1.51	4.96	4.13	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
8 mA	STD	0.63	4.87	0.05	1.08	0.45	4.96	4.13	1.38	1.51	4.96	4.13	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
12 mA	STD	0.63	3.42	0.05	1.08	0.45	1.69	1.38	3.02	3.48	1.69	1.38	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns
16 mA	STD	0.63	3.42	0.05	1.08	0.45	1.69	1.38	3.02	3.48	1.69	1.38	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.63	10.47	0.05	1.08	0.45	10.66	9.11	1.22	1.16	10.66	9.11	ns
	-1	0.55	9.21	0.04	0.95	0.39	9.38	8.01	1.26	1.20	9.38	8.01	ns
6 mA	STD	0.63	7.25	0.05	1.08	0.45	7.38	6.37	1.38	1.44	7.38	6.37	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.60	ns
8 mA	STD	0.63	7.25	0.05	1.08	0.45	7.38	6.37	1.38	1.44	7.38	6.37	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.60	ns
12 mA	STD	0.63	5.46	0.05	1.08	0.45	5.56	4.88	1.49	1.61	5.56	4.88	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.29	ns
16 mA	STD	0.63	5.46	0.05	1.08	0.45	5.56	4.88	1.49	1.61	5.56	4.88	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.29	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Timing Characteristics

Table 2-68 • 1.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	9.35	0.05	1.61	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.95	0.04	1.37	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.94	0.05	1.61	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	5.05	0.04	1.37	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns
6 mA	STD	0.64	5.22	0.05	1.61	0.46	5.09	5.22	2.11	1.93	7.59	7.718	ns
	-1	0.55	4.44	0.04	1.37	0.39	4.33	4.44	2.11	1.93	6.45	6.566	ns
8 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns
12 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns

Notes:

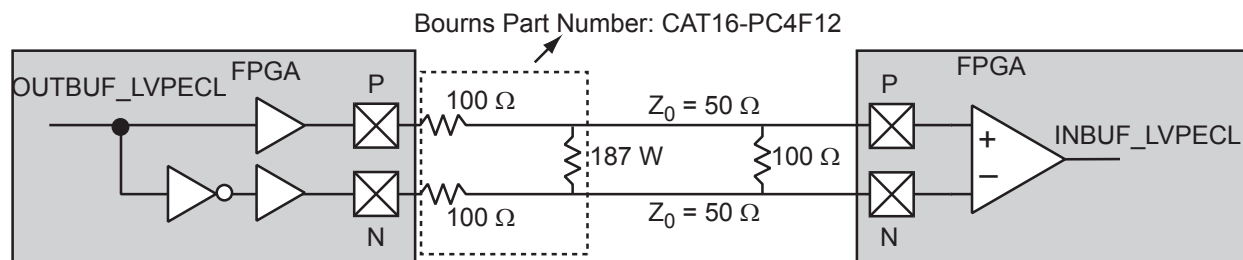
1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-69 • 1.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	14.29	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	12.16	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	11.19	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	9.52	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns
6 mA	STD	0.64	10.44	0.05	1.45	0.46	10.63	9.94	2.12	1.86	13.13	12.442	ns
	-1	0.55	8.88	0.04	1.23	0.39	9.04	8.46	2.12	1.86	11.17	10.584	ns
8 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns
12 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.


Figure 2-14 • LVPECL Circuit Diagram and Board-Level Implementation
Table 2-86 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

Note: *Measuring point = V_{trip} . See Table 2-18 on page 2-17 for a complete table of trip points.

Timing Characteristics

Table 2-88 • LVPECL

Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.64	2.01	0.05	1.57	ns
-1	0.55	1.71	0.04	1.34	ns

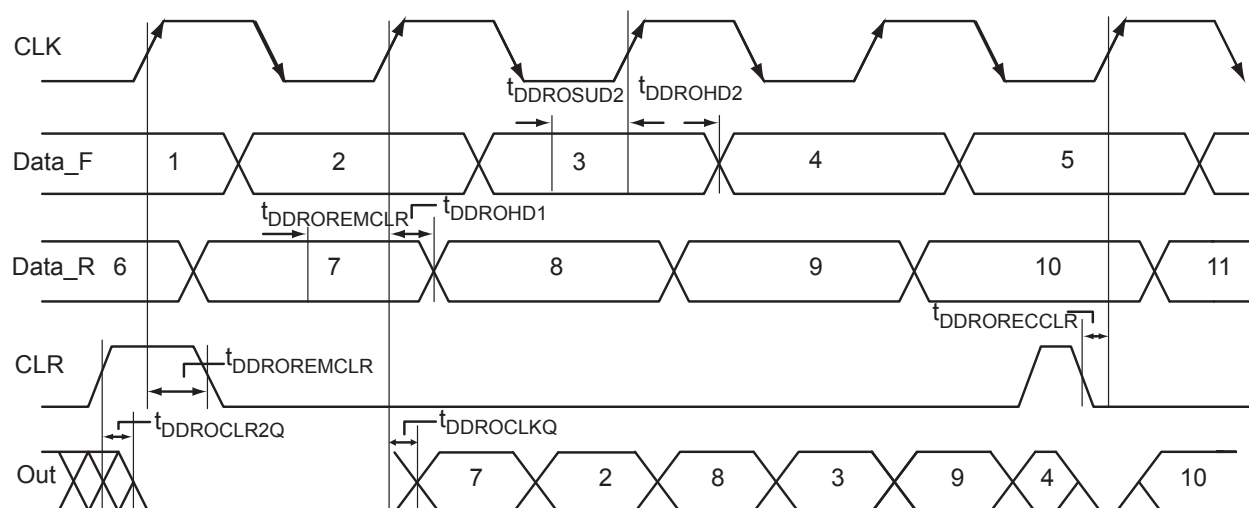
Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-89 • LVPECL

Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.63	1.95	0.05	1.52	ns
-1	0.53	1.66	0.04	1.29	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.


Figure 2-23 • Output DDR Timing Diagram

Timing Characteristics

Table 2-102 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	0.85	1.00	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.46	0.54	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.46	0.54	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	0.97	1.15	ns
$t_{\text{DDROEMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.27	0.32	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.25	0.30	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.41	0.48	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-116 • Automotive ProASIC3 CCC/PLL Specification

Parameter	Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		350	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		160 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Input Period Jitter			1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Max Peak-to-Peak Period Jitter			
	1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz	0.50%		0.70%	
24 MHz to 100 MHz	1.00%		1.20%	
100 MHz to 250 MHz	1.75%		2.00%	
250 MHz to 350 MHz	2.50%		5.60%	
Acquisition Time				
(A3P250 and A3P1000 only) LockControl = 0			300	μs
LockControl = 1			300	μs
(all other dies) LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁴				
(A3P250 and A3P1000 only) LockControl = 0			1.6	ns
LockControl = 1			1.6	ns
(all other dies) LockControl = 0			1.6	ns
LockControl = 1			0.8	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.025		5.56	ns
Delay Range in Block: Fixed Delay ^{1, 2}		2.2		ns

Notes:

1. This delay is a function of voltage and temperature. See [Table 2-5 on page 2-5](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.5\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.

Table 2-118 • RAM512X18
Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address Setup Time	0.30	0.35	ns
t_{AH}	Address Hold Time	0.00	0.00	ns
t_{ENS}	REN, WEN Setup Time	0.11	0.13	ns
t_{ENH}	REN, WEN Hold Time	0.07	0.08	ns
t_{DS}	Input data (WD) Setup Time	0.22	0.26	ns
t_{DH}	Input data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (output retained)	2.58	3.03	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.07	1.26	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.43	0.50	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.50	0.59	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.10	1.29	ns
	RESET Low to Data Out Low on RD (pipelined)	1.10	1.29	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.79	2.10	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.25	0.30	ns
t_{CYC}	Clock Cycle Time	3.85	4.53	ns
F_{MAX}	Maximum Frequency	255	217	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-119 • RAM4K9
Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address Setup Time	0.30	0.35	ns
t_{AH}	Address Hold Time	0.00	0.00	ns
t_{ENS}	REN, WEN Setup Time	0.17	0.20	ns
t_{ENH}	REN, WEN Hold Time	0.12	0.14	ns
t_{BKS}	BLK Setup Time	0.28	0.33	ns
t_{BKH}	BLK Hold Time	0.02	0.03	ns
t_{DS}	Input data (DIN) Setup Time	0.22	0.26	ns
t_{DH}	Input data (DIN) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on DOUT (output retained, WMODE = 0)	2.13	2.50	ns
	Clock High to New Data Valid on DOUT (flow-through, WMODE = 1)	2.81	3.30	ns
t_{CKQ2}	Clock High to New Data Valid on DOUT (pipelined)	1.07	1.25	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.28	0.33	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.26	0.30	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.38	0.45	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.42	0.49	ns
t_{RSTBQ}	RESET Low to Data Out Low on DOUT (flow-through)	1.10	1.29	ns
	RESET Low to Data Out Low on DOUT (pipelined)	1.10	1.29	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.79	2.10	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.25	0.30	ns
t_{CYC}	Clock Cycle Time	3.85	4.53	ns
F_{MAX}	Maximum Frequency	260	221	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

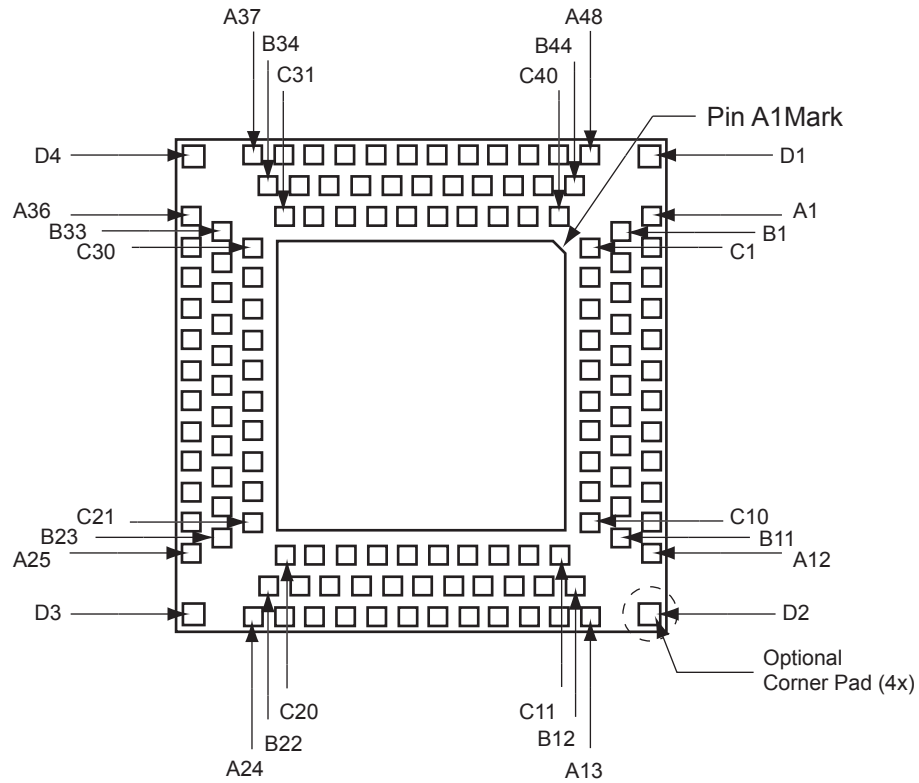
Table 2-120 • RAM512X18
Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address Setup Time	0.30	0.35	ns
t_{AH}	Address Hold Time	0.00	0.00	ns
t_{ENS}	REN, WEN Setup Time	0.11	0.13	ns
t_{ENH}	REN, WEN Hold Time	0.07	0.08	ns
t_{DS}	Input data (WD) Setup Time	0.22	0.26	ns
t_{DH}	Input data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (output retained, WMODE = 0)	2.58	3.03	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.07	1.26	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.43	0.50	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.50	0.59	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.10	1.29	ns
	RESET Low to Data Out Low on RD (pipelined)	1.10	1.29	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.79	2.10	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.25	0.30	ns
t_{CYC}	Clock Cycle Time	3.85	4.53	ns
F_{MAX}	Maximum Frequency	260	221	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

QN132



Notes:

1. This is the bottom view of the package.
2. The die attach paddle center of the package is tied to ground (GND).

Note

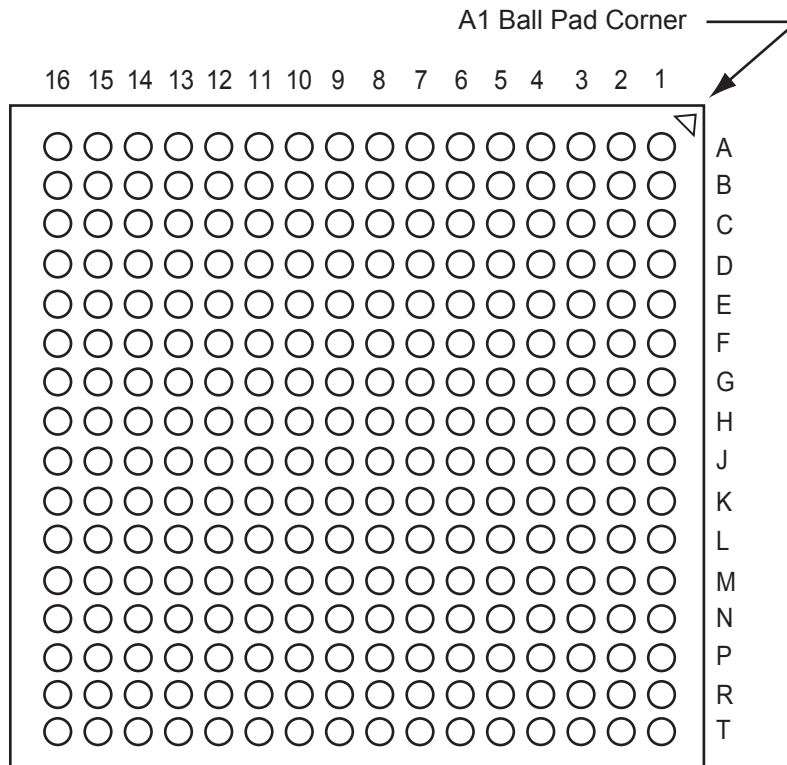
For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.actel.com/products/solutions/package/docs.aspx>.

QN132	
Pin Number	A3P250 Function
A1	GAB2/IO117UPB3
A2	IO117VPB3
A3	VCCIB3
A4	GFC1/IO110PDB3
A5	GFB0/IO109NPB3
A6	VCCPLF
A7	GFA1/IO108PPB3
A8	GFC2/IO105PPB3
A9	IO103NDB3
A10	VCC
A11	GEA1/IO98PPB3
A12	GEA0/IO98NPB3
A13	GEC2/IO95RSB2
A14	IO91RSB2
A15	VCC
A16	IO90RSB2
A17	IO87RSB2
A18	IO85RSB2
A19	IO82RSB2
A20	IO76RSB2
A21	IO70RSB2
A22	VCC
A23	GDB2/IO62RSB2
A24	TDI
A25	TRST
A26	GDC1/IO58UDB1
A27	VCC
A28	IO54NDB1
A29	IO52NDB1
A30	GCA2/IO51PPB1
A31	GCA0/IO50NPB1
A32	GCB1/IO49PDB1
A33	IO47NSB1
A34	VCC
A35	IO41NPB1
A36	GBA2/IO41PPB1

QN132	
Pin Number	A3P250 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO118VDB3
B2	GAC2/IO116UDB3
B3	GND
B4	GFC0/IO110NDB3
B5	VCOMPLF
B6	GND
B7	GFB2/IO106PSB3
B8	IO103PDB3
B9	GND
B10	GEB0/IO99NDB3
B11	VMV3
B12	GEB2/IO96RSB2
B13	IO92RSB2
B14	GND
B15	IO89RSB2
B16	IO86RSB2
B17	GND
B18	IO78RSB2
B19	IO72RSB2
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO58VDB1

QN132	
Pin Number	A3P250 Function
B25	GND
B26	IO54PDB1
B27	GCB2/IO52PDB1
B28	GND
B29	GCB0/IO49NDB1
B30	GCC1/IO48PDB1
B31	GND
B32	GBB2/IO42PDB1
B33	VMV1
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO118UDB3
C2	IO116VDB3
C3	VCC
C4	GFB1/IO109PPB3
C5	GFA0/IO108NPB3
C6	GFA2/IO107PSB3
C7	IO105NPB3
C8	VCCIB3
C9	GEB1/IO99PDB3
C10	GNDQ
C11	GEA2/IO97RSB2
C12	IO94RSB2
C13	VCCIB2
C14	IO88RSB2
C15	IO84RSB2
C16	IO80RSB2

FG256



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.actel.com/products/solutions/package/docs.aspx>.

FG256		FG256		FG256	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
G13	GCC1/IO48PPB1	K1	GFC2/IO105PDB3	M5	VMV3
G14	IO47NPB1	K2	IO107NPB3	M6	VCCIB2
G15	IO54PDB1	K3	IO104PPB3	M7	VCCIB2
G16	IO54NDB1	K4	NC	M8	NC
H1	GFB0/IO109NPB3	K5	VCCIB3	M9	IO74RSB2
H2	GFA0/IO108NDB3	K6	VCC	M10	VCCIB2
H3	GFB1/IO109PPB3	K7	GND	M11	VCCIB2
H4	VCOMPLF	K8	GND	M12	VMV2
H5	GFC0/IO110NPB3	K9	GND	M13	NC
H6	VCC	K10	GND	M14	GDB1/IO59UPB1
H7	GND	K11	VCC	M15	GDC1/IO58UDB1
H8	GND	K12	VCCIB1	M16	IO56NDB1
H9	GND	K13	IO52NPB1	N1	IO103NDB3
H10	GND	K14	IO55RSB1	N2	IO101PPB3
H11	VCC	K15	IO53NPB1	N3	GEC1/IO100PPB3
H12	GCC0/IO48NPB1	K16	IO51NDB1	N4	NC
H13	GCB1/IO49PPB1	L1	IO105NDB3	N5	GNDQ
H14	GCA0/IO50NPB1	L2	IO104NPB3	N6	GEA2/IO97RSB2
H15	NC	L3	NC	N7	IO86RSB2
H16	GCB0/IO49NPB1	L4	IO102RSB3	N8	IO82RSB2
J1	GFA2/IO107PPB3	L5	VCCIB3	N9	IO75RSB2
J2	GFA1/IO108PDB3	L6	GND	N10	IO69RSB2
J3	VCCPLF	L7	VCC	N11	IO64RSB2
J4	IO106NDB3	L8	VCC	N12	GNDQ
J5	GFB2/IO106PDB3	L9	VCC	N13	NC
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO58VDB1
J8	GND	L12	VCCIB1	N16	GDA1/IO60UDB1
J9	GND	L13	GDB0/IO59VPB1	P1	GEB1/IO99PDB3
J10	GND	L14	IO57VDB1	P2	GEB0/IO99NDB3
J11	VCC	L15	IO57UDB1	P3	NC
J12	GCB2/IO52PPB1	L16	IO56PDB1	P4	NC
J13	GCA1/IO50PPB1	M1	IO103PDB3	P5	IO92RSB2
J14	GCC2/IO53PPB1	M2	NC	P6	IO89RSB2
J15	NC	M3	IO101NPB3	P7	IO85RSB2
J16	GCA2/IO51PDB1	M4	GEC0/IO100NPB3	P8	IO81RSB2

